ABSTRACT

The invention concerns a method for transferring an electrically active thin film from an initial substrate to a target substrate, comprising the following steps:

- ion implantation through one face of said initial substrate in order to create a buried, embrittled film at a determined depth in relation to the implanted face of the initial substrate, a thin film thus being delimited between the implanted face and the buried face;

- fastening the implanted face of the initial substrate with a face of the target substrate;

- separating the thin film from the remainder of the initial substrate at the level of the buried film;

- thinning down the thin film transferred on the target substrate.

The implantation dosage, energy and current are chosen, during the ion implantation stage, so that the concentration in implantation defects is less than a determined threshold, resulting in, within the thinned down thin film, a number of acceptor defects that is compatible with the desired electrical properties of the thin film.

No figure.